



Attorney's Docket No.: 079-163003 / US3375D1D1

\$2813

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Yamazaki, et al. Art Unit : 2813
Serial No.: 09/898,986 Examiner : Laura Schillinger
Filed : July 3, 2001
Title : SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING
THE SAME

Commissioner for Patents
Washington, D.C. 20231

TRANSMITTAL LETTER

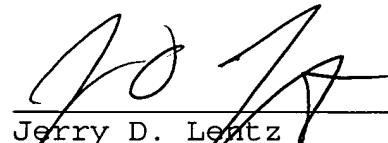
Correspondence relating to this application is enclosed.
The required fees are computed below. Please apply any charges
not covered, or any credits, to Deposit Account No. 06-1050.

Total					
Claims	63	-	31	=	32 \$576
Independent	7	-	4	=	3 \$252
Information Disclosure Statement					\$180
TOTAL FEE DUE					\$1,008

A check for \$1,008 is attached.

Respectfully submitted,

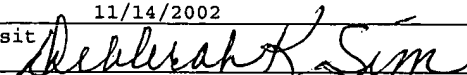
Date: 11/14/02


Jerry D. Lentz
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Debbrah K. Sim
Typed or Printed Name of Person Signing
Certificate



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#71B
12-27-2
Robert
amdt

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RESPONSE

In response to the action mailed August 14, 2002, please
amend the application as follows:

In the claims:

Please amend claims 1, 2, 6, 7, and 11 as follows:

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B --1. (Amended) A method of manufacturing a semiconductor
device, comprising the steps of:

forming first and second semiconductor islands on an
insulating surface;

introducing ions of a p-type impurity into at least a
portion of only said first semiconductor island without mass
separation wherein said portion is to become a channel region of
a thin film transistor; and

11/22/2002 HDEMESS1 00000059 09898986

01 FC:1201 252.00 OP
02 FC:1202 576.00 OP

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